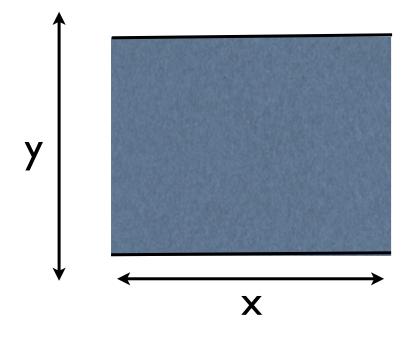
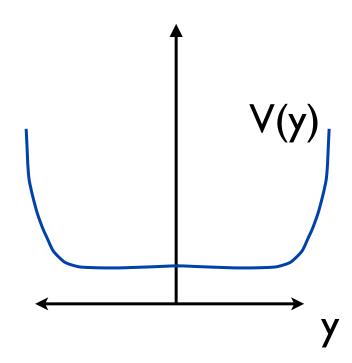
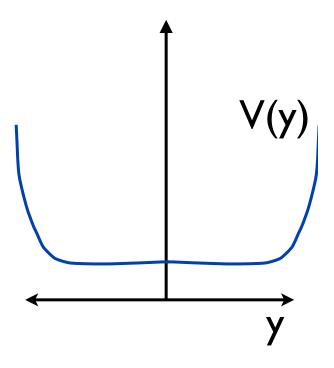
- A simple way to understand the quantization of Hall effect, realized by Halperin
- Consider Hall bar







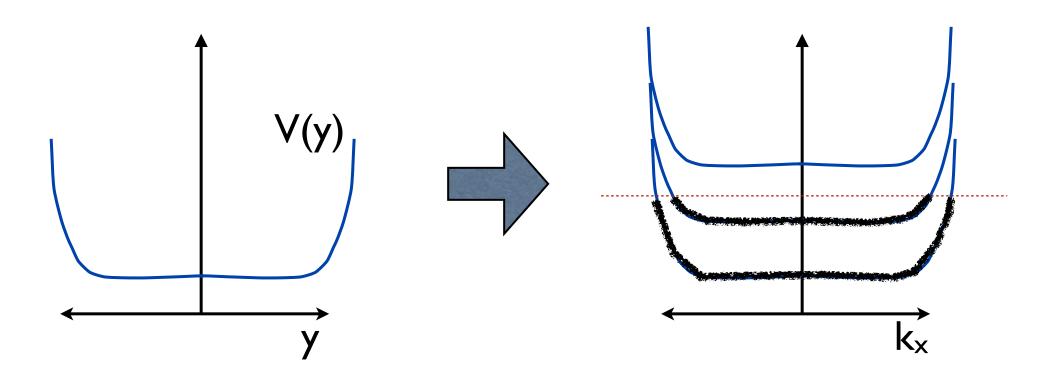
$$\left[-\frac{\hbar^2}{2m} \frac{d^2}{dy^2} + \frac{1}{2} m\omega_c^2 (y - k_x \ell^2)^2 + V(y) \right] Y = \epsilon Y$$

If V(y) is slowly varying, then we can approximate

$$V(y) \approx V(k_x \ell^2)$$

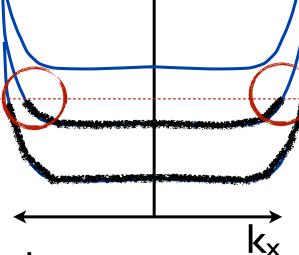
$$\epsilon_n \approx \hbar\omega_c(n+\frac{1}{2}) + V(k_x\ell^2)$$

$$\epsilon_n \approx \hbar\omega_c(n+\frac{1}{2}) + V(k_x\ell^2)$$



Low energy states at the edges of the system

$$\epsilon_n \approx \hbar\omega_c(n+\frac{1}{2}) + V(k_x\ell^2)$$

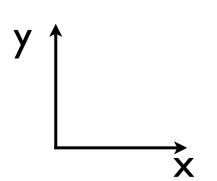


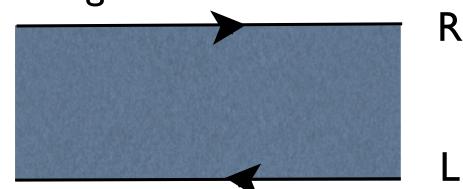
Near the edge, we can linearize the energy

$$k_x = \pm K_n + q_x$$

$$\epsilon_n pprox \epsilon_F \pm v_n q_x$$

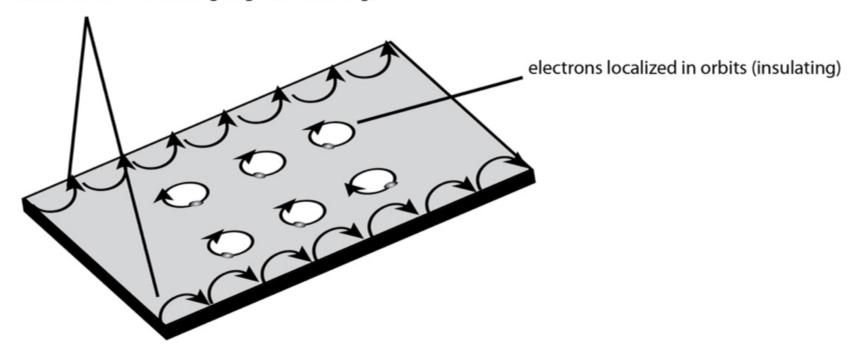
 This describes "right and left-moving chiral fermions" = edge states



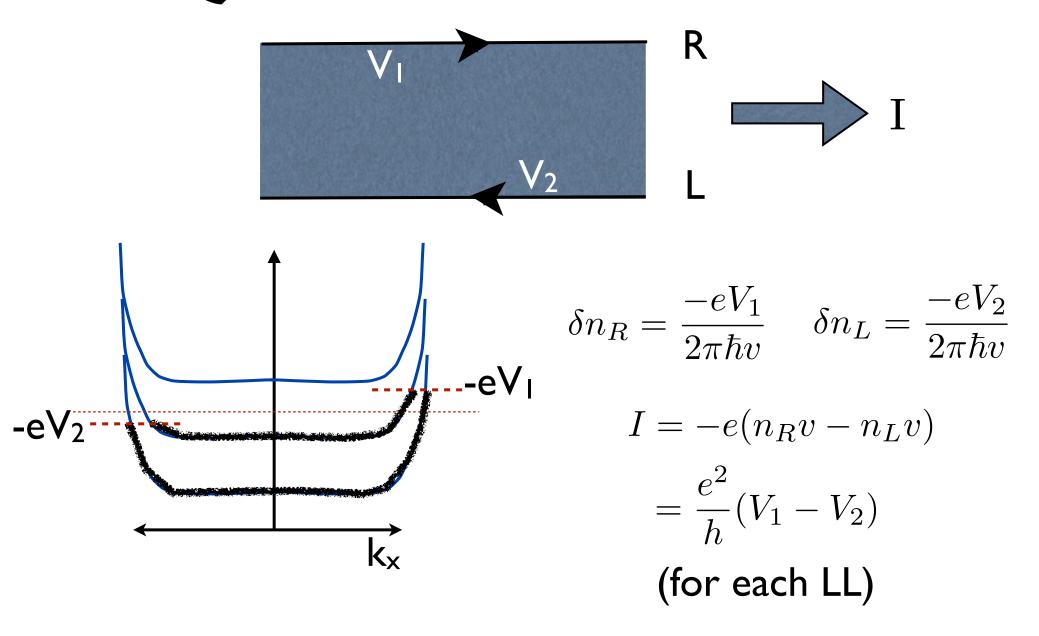


Corresponds to semi-classical "skipping orbits"

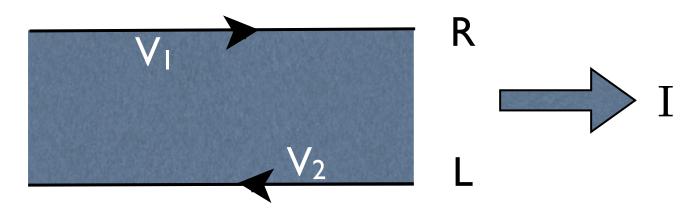
electrons can move along edge (conducting)



Quantum Hall effect



Quantum Hall effect



$$I_x = N \frac{e^2}{h} V_y$$
 $G_{xy} = N \frac{e^2}{h}$ n.b. h/e² = 25 kOhms

$$G_{xy} =$$

n.b.
$$h/e^2 = 25 \text{ kOhms}$$

$$V_r = 0$$

R+L movers are separately at equilibrium. No dissipation

$$\begin{array}{c}
10 \\
10 \\
0 \\
0
\end{array}$$

$$\begin{array}{c}
i = 2 \\
i = 3
\end{array}$$

$$\begin{array}{c}
i = 3 \\
0 \\
0
\end{array}$$

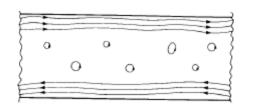
$$\begin{array}{c}
i = 3 \\
7 \\
T
\end{array}$$

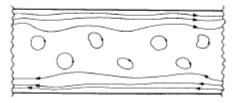
$$\sigma_{xx} = \rho_{xx} = 0$$

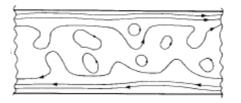
Show these are equivalent!!

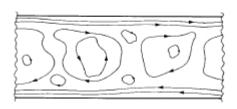
Robustness

- In real samples, disorder is important, and splits the degeneracy of the bulk LL states
- BUT...it cannot "back-scatter" from one edge to another - "protected" edge state





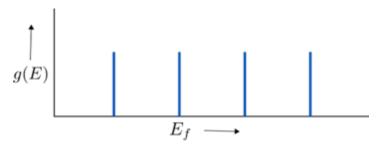


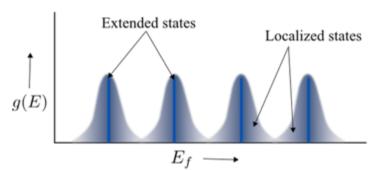


"peels off" from boundary and crosses the bulk

Robustness

- In real samples, disorder is important, and splits the degeneracy of the bulk LL states
- BUT...it cannot "back-scatter" from one edge to another





it turns out truly delocalized states occur only at one energy...this is NOT obvious

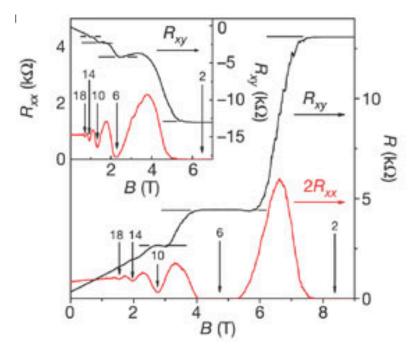
consequently, IQHE "steps" in Hall conductance are expected to be infinitely sharp at T=0, for a large sample

IQHE phases

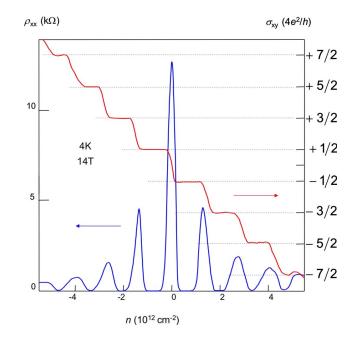
- Actually, the states with different integer quantum Hall conductivity are different phases of matter at T=0: they are sharply and qualitatively distinguished from one another by σ_{xy}
- This means that to pass from one IQHE state to another requires a quantum phase transition: this corresponds to the point at which the edge state delocalizes and "percolates" through the bulk
- However, unlike most phases of matter, IQHE states break no symmetry
- They are distinguished not by symmetry but by "topology" (actually the Hall conductivity can be related to topology...a bit of a long story)

Graphene IQHE

What first experiments saw...



Zhang et al, 2005



Novoselov et al, 2005

$$\sigma_{xy} = \frac{e^2}{h} \times (\pm 2, \pm 6, \pm 10, \cdots)$$

Relativistic vs NR LLs

- We expect σ_{xy} to change by $\pm e^2/h$ for each filled Landau level
- Each Landau level is
- 4-fold degenerate
 - 2 (spin) * 2 (K,K')

Consistent with observations, but zero is not fixed

0

Fermi level is "in the middle" of 0th LL in undoped graphene

Relativistic vs NR LLs

• Guess: when $E_F=0$, there are equal numbers of holes and electrons: $\sigma_{xy}=0$

Then we get the observed sequence

10 6

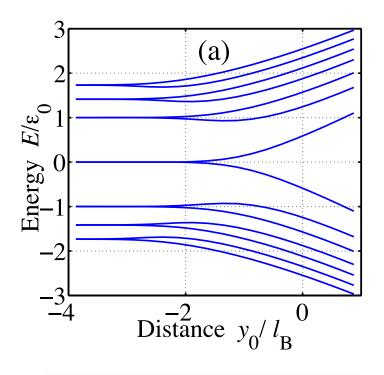
0 —-2

Fermi level is "in the middle" of 0th LL in undoped graphene

Edge state picture

We will not work this out here, but one can show that levels at the edge bend as shown here

The downward bending of half the levels naturally explains the observed quantization, and why the filled valence states do not contribute to σ_{xy}



the splitting of n != 0 levels shown is due to lifting of the spin/valley degeneracy, which we have not talked about.

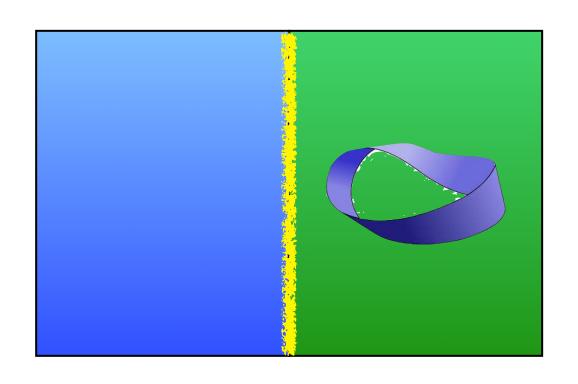
This leads to additional integer states at higher fields.

Topological Insulators

- So the IQHE states are examples of what we now call "Topological Insulators": states which are distinguished by "protected" edge states
- Until very recently, it was thought that this physics was restricted to high magnetic fields and 2 dimensions
- But it turns out there are other Tls...even in zero field and in both 2d and 3d!

Topological insulators

 General understanding: insulators can have gaps that are "non-trivial": electron wavefunctions of filled bands are "wound differently" than those of ordinary insulators



"unwinding" of wavefunctions requires gapless edge states

Topological insulators

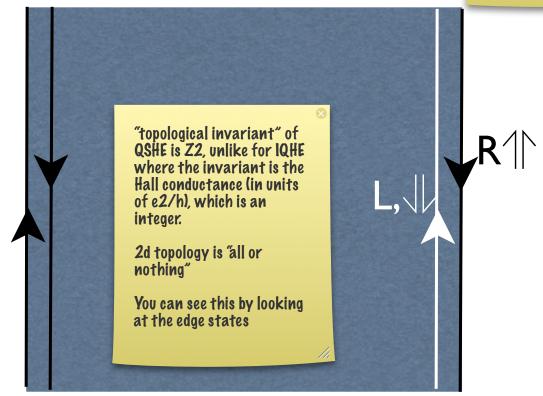
- 2005: Kane+Mele "Quantum spin Hall effect": 2d materials with SOC can show protected edge states in zero magnetic field
- 2007: QSHE now called 2d "Z2" topological insulator
 found experimentally in HgTe/CdTe quantum wells
- 2007: Z₂ topological insulators predicted in 3d materials
- 2008: First experiments on Bi_{1-x}Sb_x start wave of 3d
 TIs

Since then there has been explosive growth

QSHE

Edge states!

To preserve timereversal symmetry, there
must be counterpropagating edge states,
and no net spin
(magnetization)



like IQHE but with counter-propagating edge states for opposite spin